Abstracts

High Power Pulsed UHF and L-Band p/sup +/-n-n/sup +/ Silicon TRAPATT Diode Oscillators

C.O.G. Obah, E. Benko, H.C. Bowers and T.A. Midford. "High Power Pulsed UHF and L-Band p/sup +/-n-n/sup +/ Silicon TRAPATT Diode Oscillators." 1975 MTT-S International Microwave Symposium Digest of Technical Papers 75.1 (1975 [MWSYM]): 88-90.

TRAPATT oscillators utilizing highly graded p/sup +/-n-n/sup +/ silicon junction devices with large p-region width to total depletion region width ratios have produced more than 500 W pulsed power output with a minimum efficiency of 25% in the UHF and L-band ranges.

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